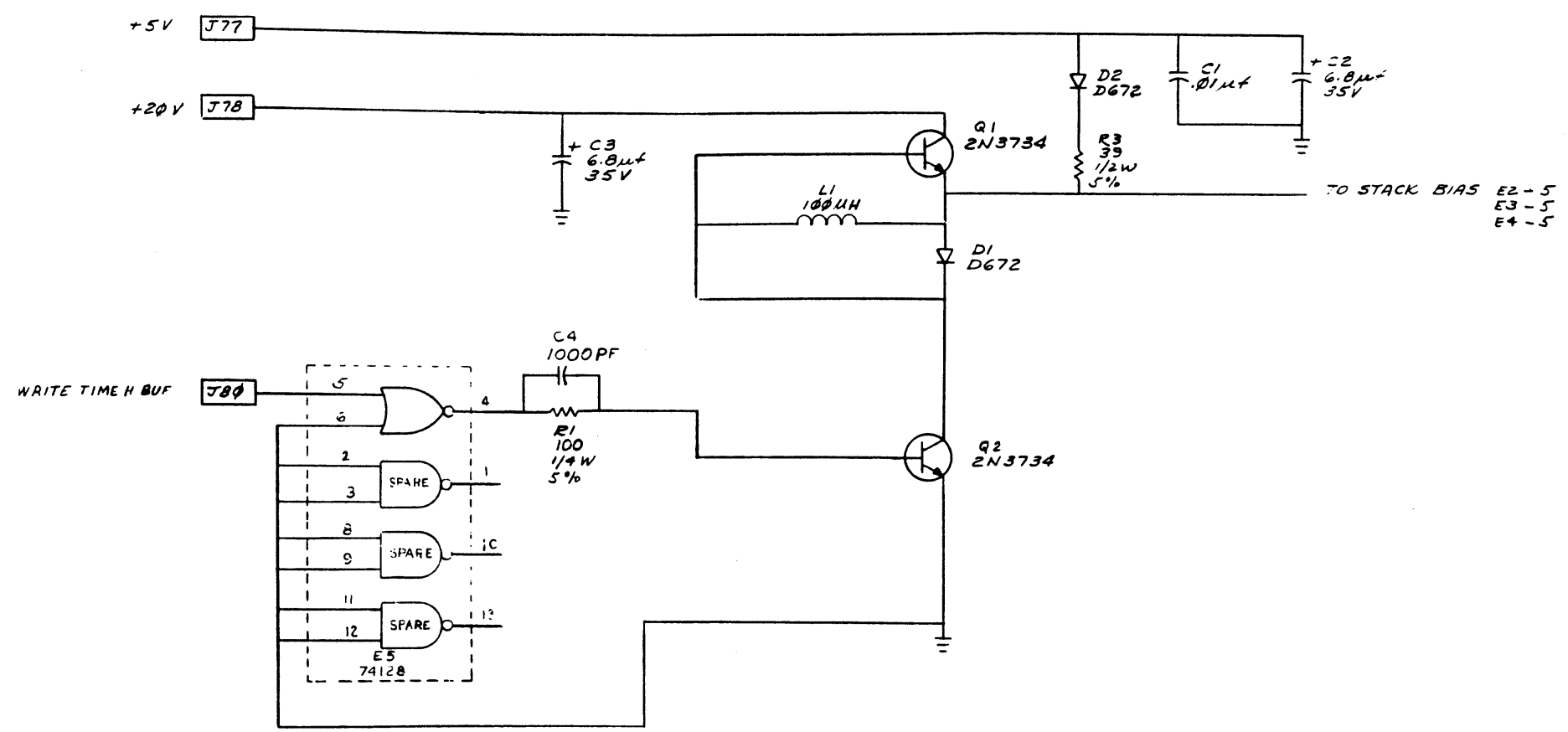


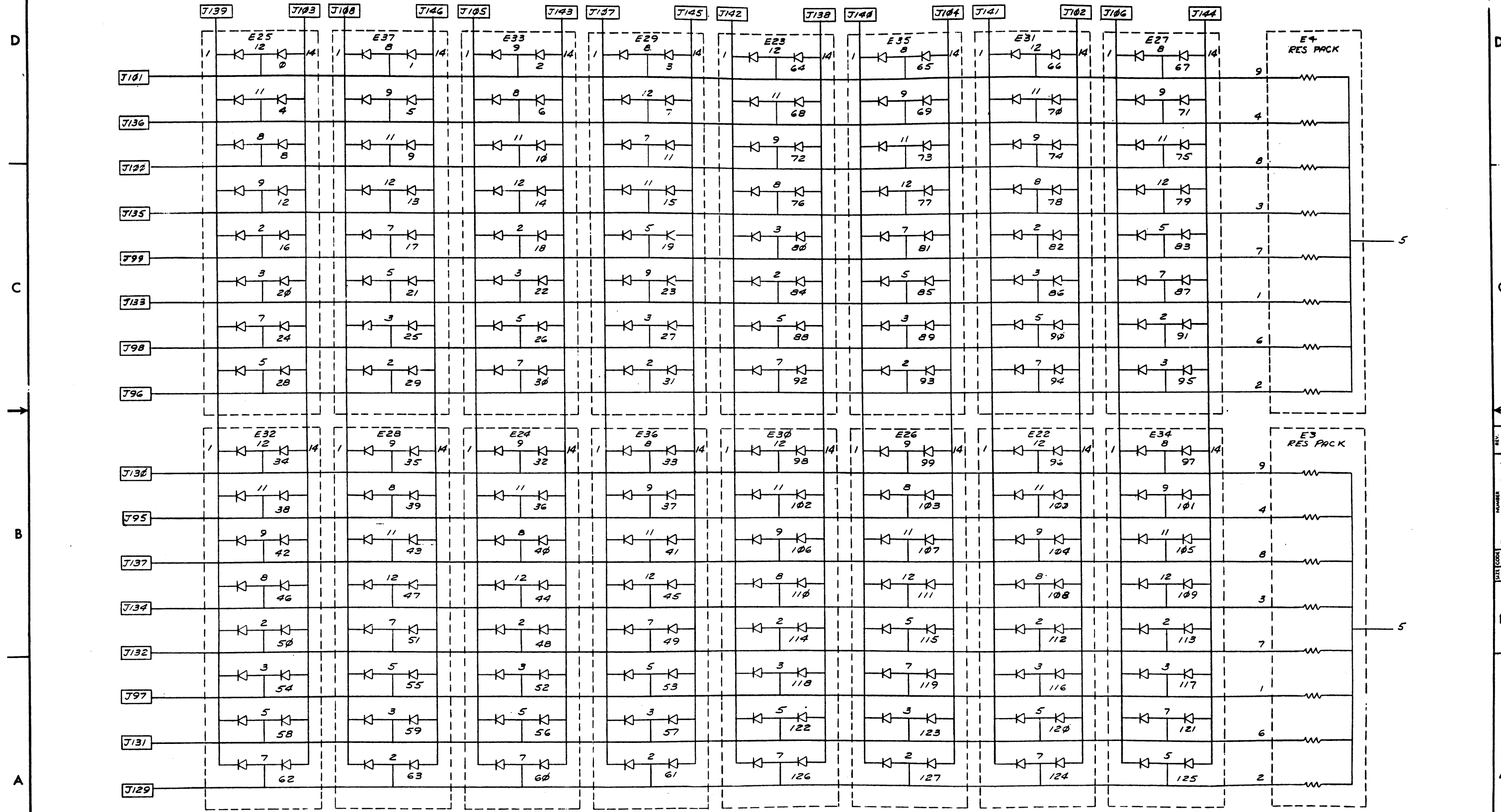
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REVISIONS		
CHK	CHANGE NO.	REV.

REV. A DCS 5411531-0-1

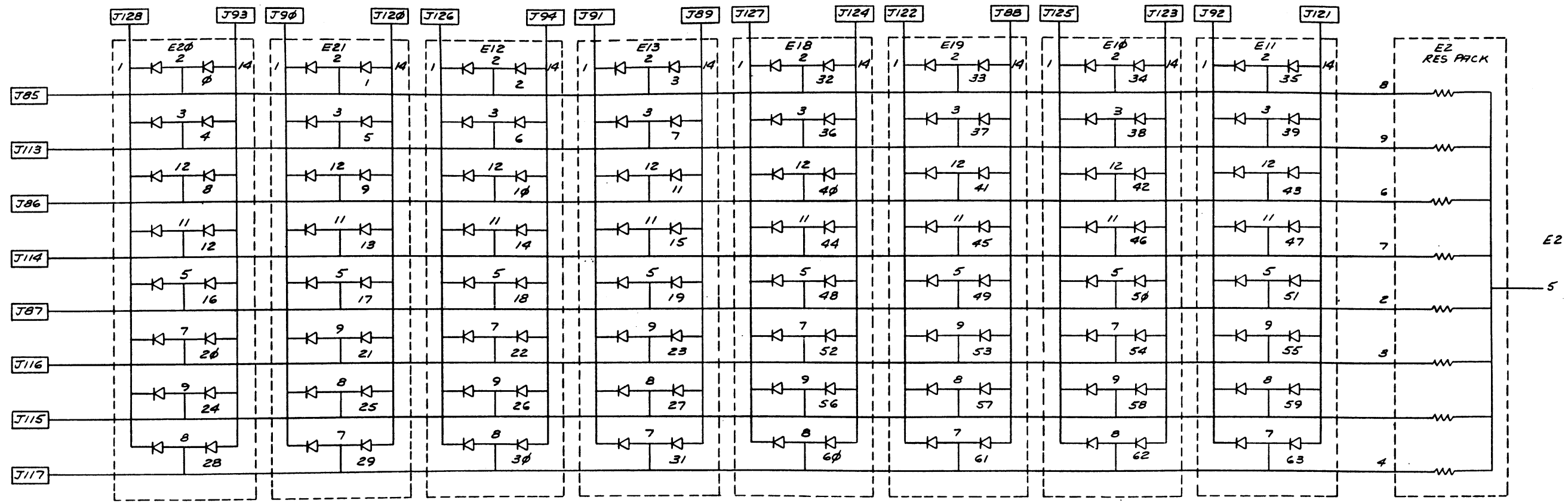
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REVISIONS		
CHK	CHANGE NO.	REV.

TITLE CORE MEMORY STACK 8K		SIZE CODE DCS	NUMBER 5411531-0-1	REV. A
SCALE	SHEET 3 OF 4	DIST.		

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REVISIONS		
CHK	CHANGE NO.	REV.

"Y" DRIVE DIMENSION DIODE MATRIX

TITLE	CORE MEMORY STACK	SIZE CODE	8K	NUMBER	DCS 5411531-0-1	REV.	A
SCALE	+	SHEET	4	OF	4	DIST.	

DCS 5411531-0-1

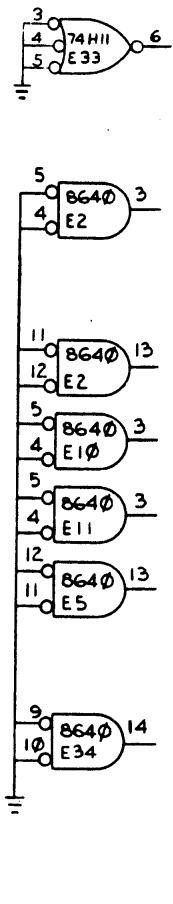
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NOTES:

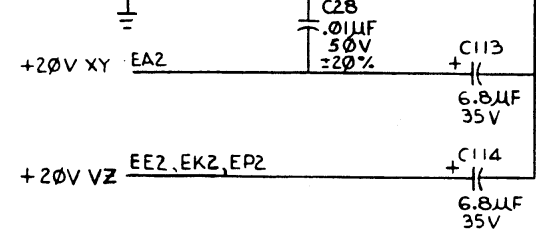
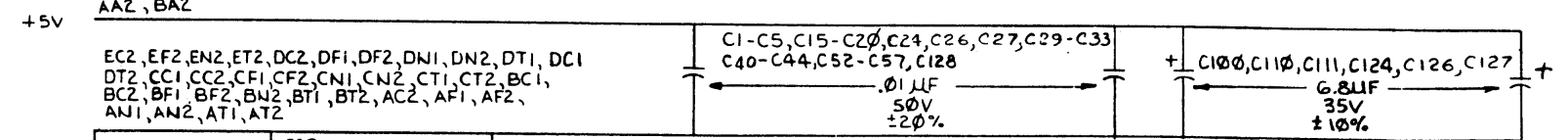
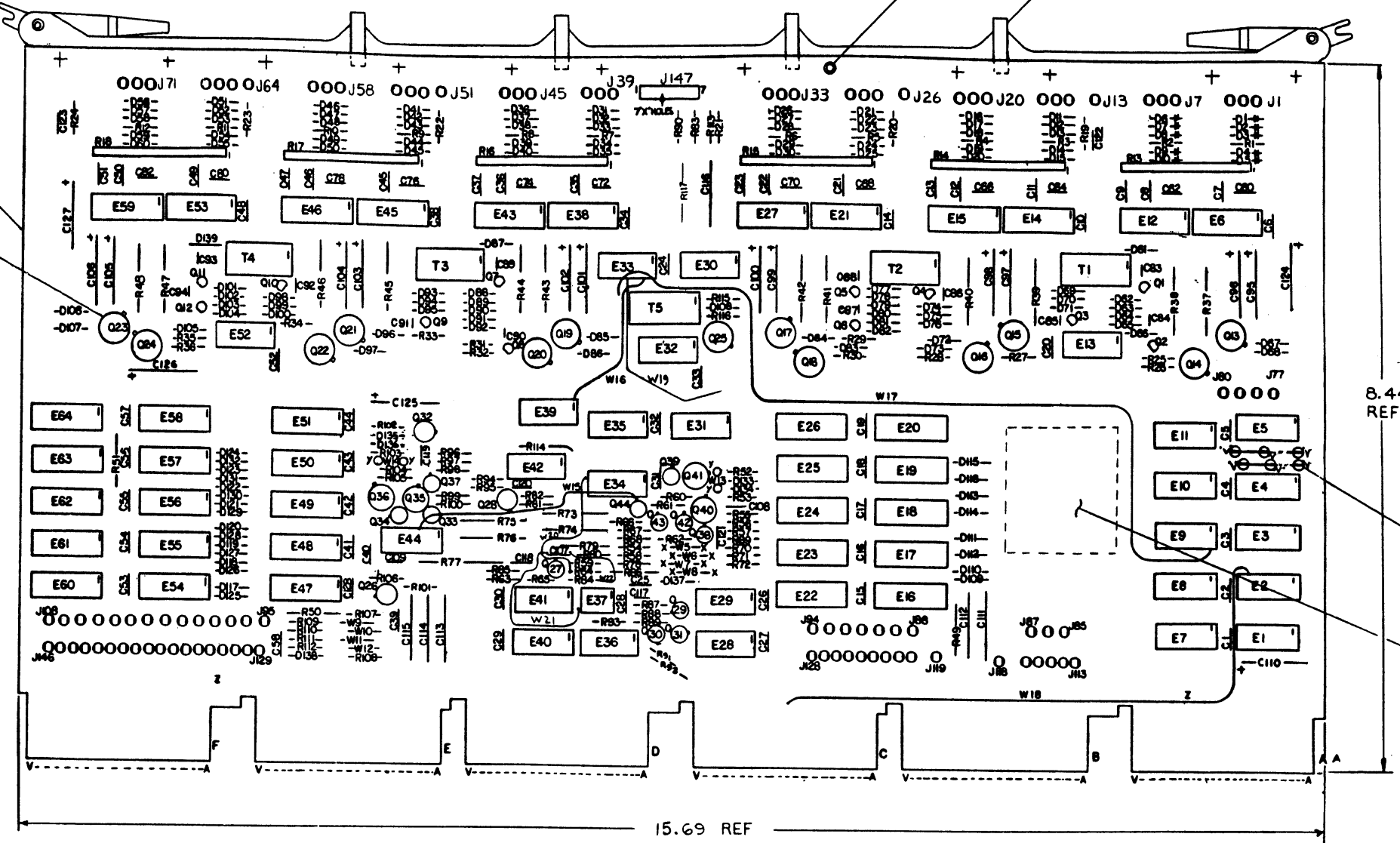
- UNLESS OTHERWISE SPECIFIED:
 - RESISTORS ARE 1/4W, ±5%
 - CAPACITORS ARE 50V
 - DIODES ARE D672
- ALL RECEPTACLES ARE INDICATED WITH J NO'S.
- C59, C61, C63, C65, C67, C69, C71, C73, C75, C77, C79 & C81 ARE NOT USED.
- MEMORY TEST IS ALLOWED TO MAKE THE FOLLOWING COMPONENT SUBSTITUTION
 R108-3.48K 1% 1/4W PART #13-05114-00
 R69-357K 1/8W 1% PART #13-05421-00
- STAMP MEM. SELECTION SCHEME IN MEMORY TEST.
 DEFINITION OF MEMORY SELECTION JUMPERS WITH MEMORY IS DECODED FOR MEMORY BANK SELECTED

LOCATION	MEMORY ADDRESSES	MEMORY BANK SELECTED
1 E1	0 TO 8K	1ST 8K
2 E2	8K TO 16K	2ND 8K
3 E3	16K TO 24K	3RD 8K
4 E4	24K TO 32K	4TH 8K

6. MEM. SELECT TO BE STAMPED ON THE MEMORY TEST AREA



SPARES



IC TYPE	-5V	GND	+5V	+20V
75325				16
7520	8			16
8640	1		8	
7442		8		16
741		4		7
384		1	8	

GND AND 5V ARE USUALLY PIN 7 AND 14 RESPECTIVELY EXCEPT AS STATED ABOVE

IC PIN LOCATIONS

REVISIONS

CHK	CHANGE NO.	REV.
C. GRANGER	1	10/24/74
C. GRANGER	2	11/5/74
C. GRANGER	3	1/17/75
C. GRANGER	4	5/4/77
C. GRANGER	5	10/26/78
C. GRANGER	6	14-OCT-76
C. GRANGER	7	11-0005A-D
C. GRANGER	8	7-1-75
C. GRANGER	9	6-6-75
C. GRANGER	10	6649-00003 B2
C. GRANGER	11	5-7
C. GRANGER	12	4-16-75
C. GRANGER	13	6649-00002 B1

QTY REF. DESIGNATION DESCRIPTION PART NO. ITEM NO.

FIRST USED ON OPTION MODEL PDP8-A

ETCH BOARD REV. E

DATE 10/24/74

DATE 11/5/74

DATE 1/17/75

DATE 5/4/77

DATE 10/26/78

DATE 14-OCT-76

DATE 11-0005A-D

DATE 7-1-75

DATE 6-6-75

DATE 6649-00003 B2

DATE 5-7

DATE 4-16-75

DATE 6649-00002 B1

DATE 6649-0-1

REV F

SCALE 1 OF 12

SHEET 1 OF 12

SEMICONDUCTOR CONVERSION CHART

8K, 12 BIT (B1) BASE BOARD

DIGITAL